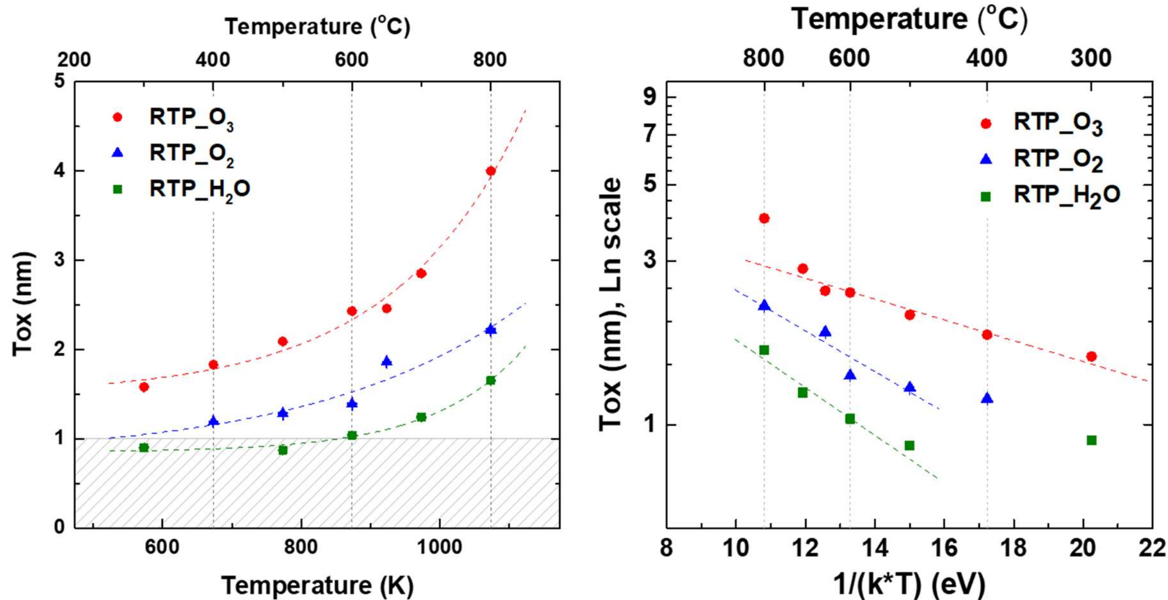

Figure 1. Oxidation of silicon using H_2O, O_2, and O_3 at different temperatures and Arrhenius plots for 20 mins oxidation.

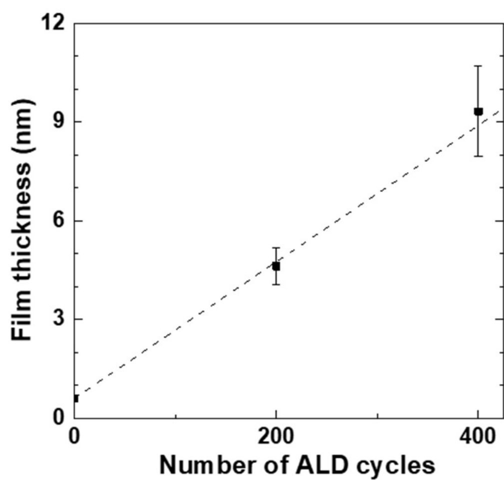

Figure 2. Thickness of SiO_2 film deposited as a function of number of cycles.

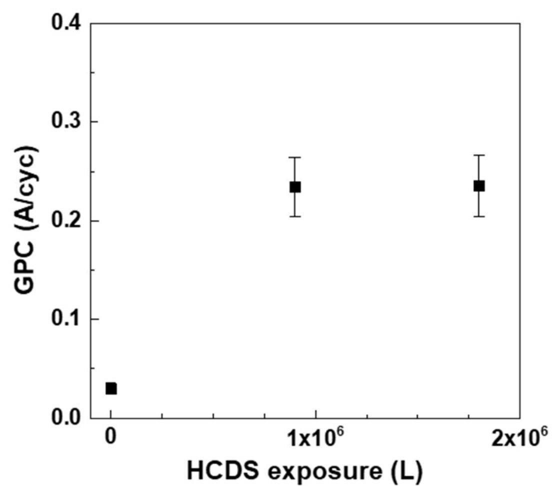

Figure 3. Growth rate of ALD SiO_2 as a function of Si_2Cl_6 exposure